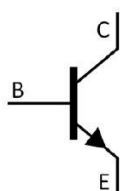
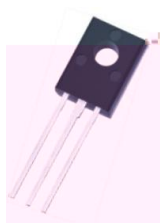


WR0459I M M E QSQ Æ M ç s ll 1 Silicon NPN transistor in a TO-126F Plastic Package.

High V_{CEO} , high f_T .

27MHz CB transceiver driver applications.



PIN1 χ Emitter

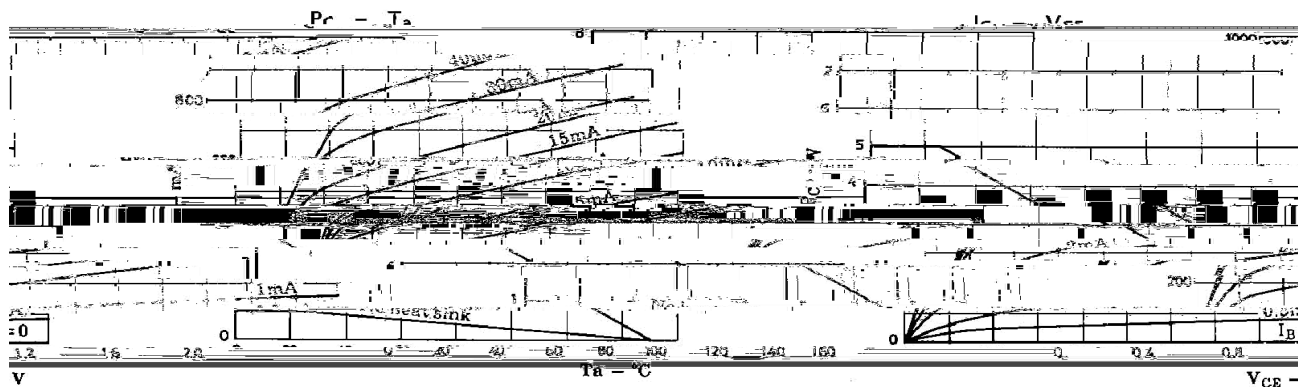
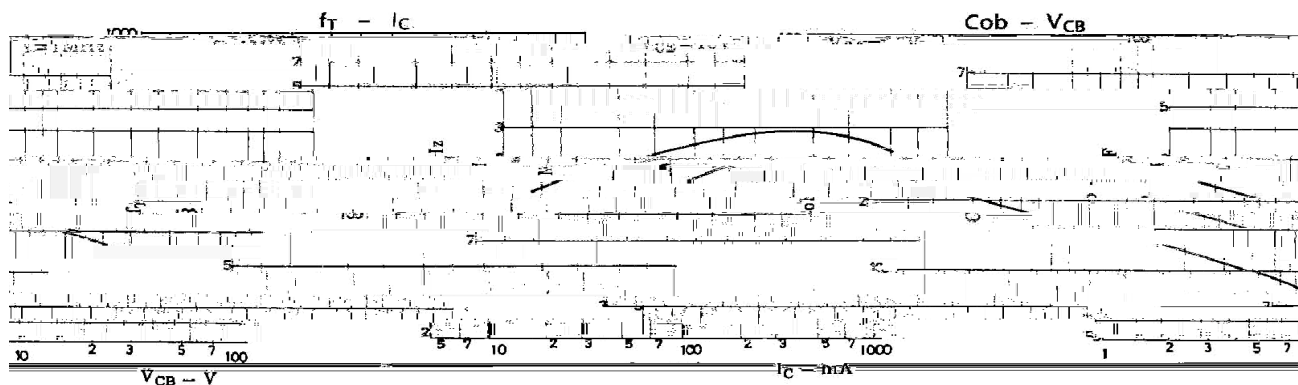
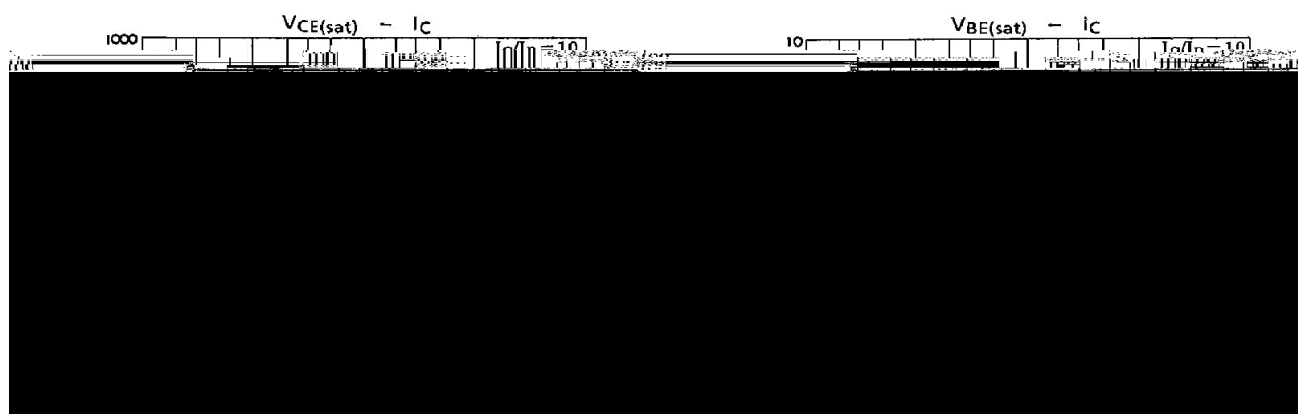
PIN 2 χ Collector

PIN 3 χ Base

/ h

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	75	V
Collector to Emitter Voltage	V_{CER}	75	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Collector Current – Continuous(Pulse)	I_{CP}	1.5	A

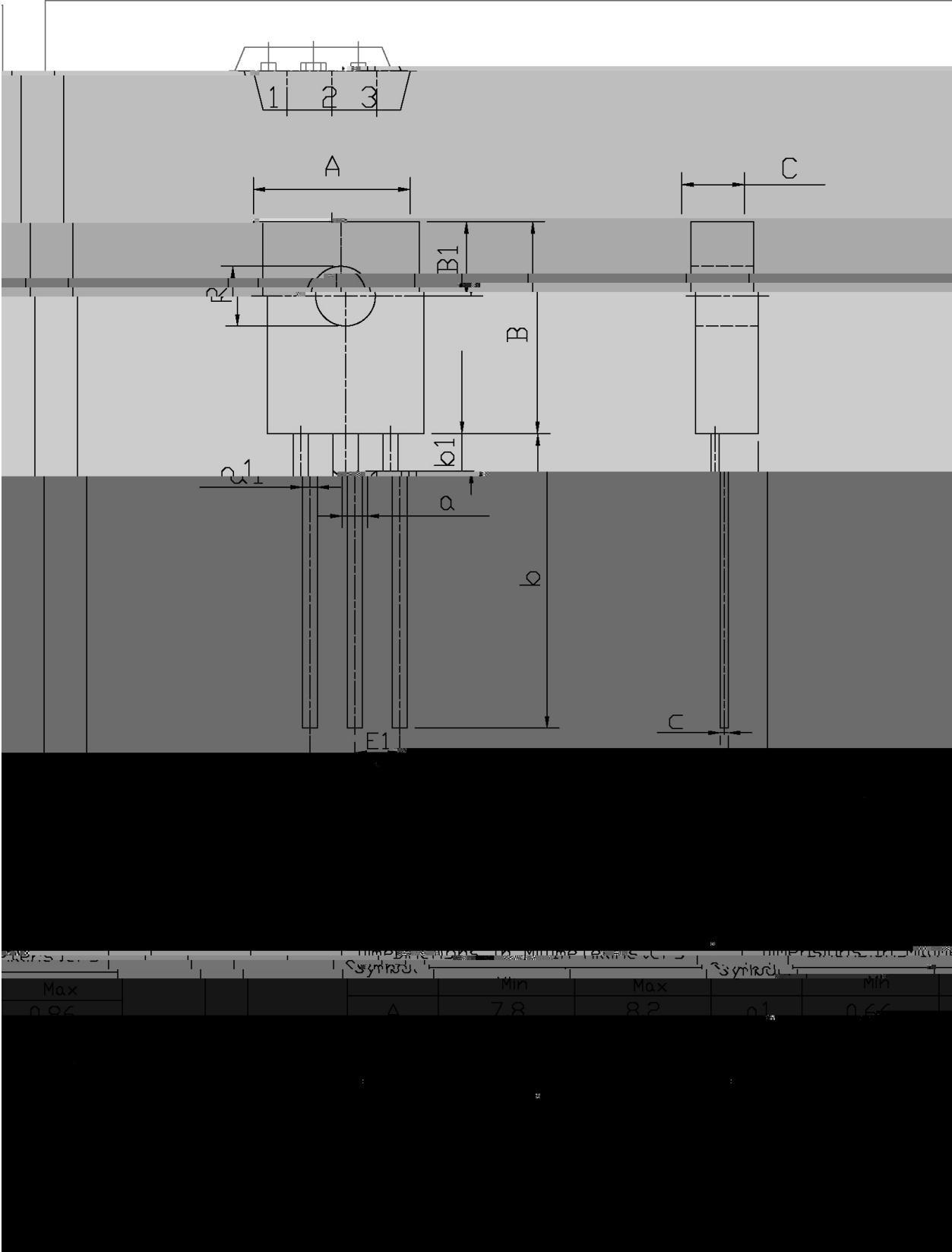
/ Electrical Characteristic Curve



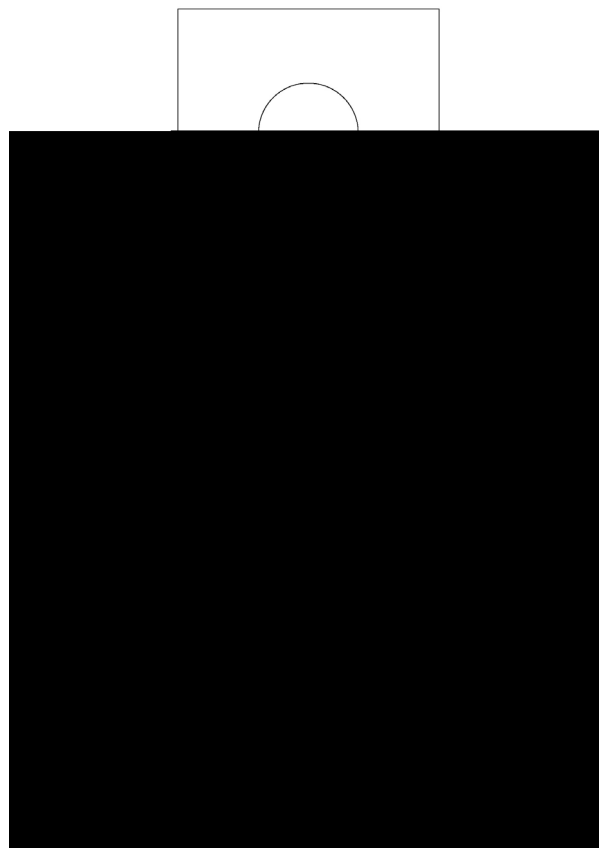
/ Package Dimensions

1U-126F

单位: mm



/ Marking Instructions



б " X

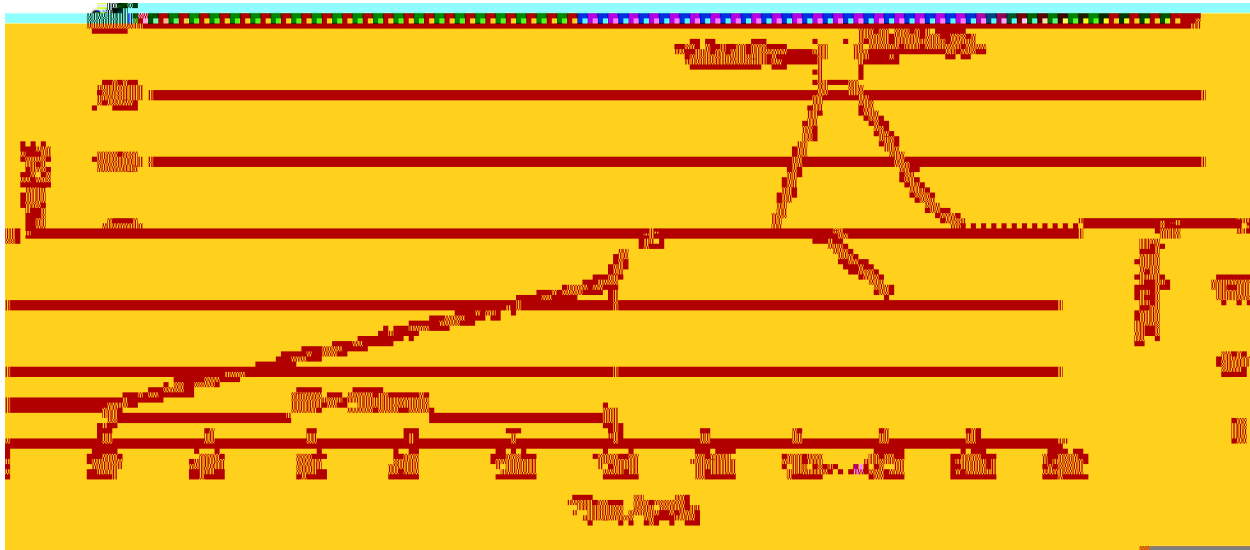
EU X

F5647 X

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() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. Preheating: 25~150 °C, Time: 60~90sec;
2. 2. Peak Temp.: 255 °C, Duration: 5 °C 0.5sec;
3. 3. Cooling Speed: 2~10 °C /sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 255 °C, Duration: 5 °C 0.5sec.
3. Cooling Speed: 2~10 °C /sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 ± 5 °C °C 10 ± 1 sec. Temp.: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

“Q” γ t / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

“γ” γ t / TUBE

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm ³)
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